

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) An ID label comprising:  
a label substratum over which an antenna is formed;  
a thin film integrated circuit device including a thin film transistor, provided in contact with the label substratum;  
a separating sheet; and  
an adhesive provided between the label substratum and the separating sheet,  
wherein the separating sheet is configured to be peeled from the adhesive.
2. (Original) The ID label according to claim 1, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.
3. (Original) The ID label according to claim 1, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of an upper surface and a lower surface of the thin film integrated circuit device.
4. (Currently Amended) The ID label according to claim 1, wherein in the case where [[the]] a protective layer is formed on [[the]] an upper surface and [[the]] a lower surface of the thin film integrated circuit device, it is placed the thin film integrated circuit device at a position of  $(d/2) \pm 30 \mu\text{m}$  or less when a total thickness of the thin film integrated circuit device and the top and bottom protective films is  $d$ .

5. (Original) The ID label according to claim 1, wherein a semiconductor film of the thin film transistor included in the thin film integrated circuit device contains hydrogen or halogen of 0.0005 to 5 atomic %.

6. (Previously Presented) The ID label according to claim 1, wherein a size of the thin film integrated circuit device is 0.09 to 25 mm<sup>2</sup>.

7. (Original) The ID label according to claim 1, wherein a thickness of the thin film integrated circuit device is 0.1 to 3  $\mu$ m.

8. (Currently Amended) An ID label comprising:  
an internal substratum over which an antenna is formed;  
a label substratum;  
a thin film integrated circuit device including a thin film transistor, provided in contact with the internal substratum;  
a separating sheet; and  
an adhesive provided between the label substratum and the separating sheet,  
wherein the separating sheet is configured to be peeled from the adhesive.

9. (Original) The ID label according to claim 8, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

10. (Original) The ID label according to claim 8, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of an upper portion and a lower portion of the thin film integrated circuit device.

11. (Currently Amended) The ID label according to claim 8, wherein in the case where [[the]] a protective layer is formed on [[the]] an upper surface and [[the]] a lower

surface of the thin film integrated circuit device, it is placed the thin film integrated circuit device at a position of  $(d/2) \pm 30 \mu\text{m}$  or less when a total thickness of the thin film integrated circuit device and the top and bottom protective films is  $d$ .

12. (Original) The ID label according to claim 8, wherein a semiconductor film of the thin film transistor included in the thin film integrated circuit device contains hydrogen or halogen of 0.0005 to 5 atomic %.

13. (Previously Presented) The ID label according to claim 8, wherein a size of the thin film integrated circuit device is  $0.09$  to  $25 \text{ mm}^2$ .

14. (Original) The ID label according to claim 8, wherein a thickness of the thin film integrated circuit device is  $0.1$  to  $3 \mu\text{m}$ .

15. (Currently Amended) An ID card comprising:  
a card substratum over which an antenna is formed;  
an insulating layer over the antenna;  
a wiring formed on the insulating layer;  
a thin film integrated circuit device including a thin film transistor, provided in contact with the card substratum; and  
a cover for covering at least a side of the card substratum where ~~[[an]]~~ the antenna and the thin film integrated circuit device are formed,  
wherein the wiring is connected to the antenna through a contact hole formed in the insulating layer.

16. (Original) The ID card according to claim 15, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

17. (Original) The ID card according to claim 15, wherein the cover comprises resin and is formed by a laminating method.

18. (Currently Amended) The ID card according to claim 15, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of ~~[[the]]~~ an upper surface and ~~[[the]]~~ a lower surface of the thin film integrated circuit device.

19. (Currently Amended) An ID card comprising:  
an internal substratum ~~over which an antenna is formed~~ having a first surface and a second surface opposing to the first surface;  
an antenna formed over the first surface of the internal substratum;  
a thin film integrated circuit device including a thin film transistor, ~~provided in contact with internal substratum~~ over the first surface;  
a wiring formed on the second surface of the internal substratum; and  
a cover for covering around the internal substratum,  
wherein the wiring is electrically connected to the thin film transistor and a part of the antenna through a contact hole formed in the internal substratum.

20. (Original) The ID card according to claim 19, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

21. (Original) The ID card according to claim 19, wherein the cover comprises resin and is formed by a laminating method.

22. (Currently Amended) The ID card according to claim 19, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of ~~[[the]]~~ an upper surface and ~~[[the]]~~ a lower surface of the thin film integrated circuit device.

23. (Currently Amended) An ID tag comprising:  
a thin film integrated circuit device including a thin film transistor provided in contact with a substratum on which an antenna is formed; [[and]]  
an insulating layer over the antenna;  
a wiring formed over the insulating layer; and  
a cover for covering at least a side in which the antenna and the thin film integrated circuit device are formed in the substratum,  
wherein the wiring is connected to the antenna through a contact hole formed in the insulating layer.

24. (Original) The ID tag according to claim 23, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

25. (Original) The ID tag according to claim 23, wherein the cover comprises resin and is formed by a laminating method.

26. (Currently Amended) The ID tag according to claim 23, wherein a protective layer comprising a single layer of stacked layers containing silicon oxide, silicon nitride of silicon oxynitride is formed on at least one of [[the]] an upper surface and [[the]] a lower surface of the thin film integrated circuit device.

27. (Currently Ameded) An ID tag comprising:  
an internal substratum having a first surface and a second surface opposing to the first surface;  
an antenna formed over the first surface of the internal substratum;  
a thin film integrated circuit device including a thin film transistor provided in contact with an internal substratum on which an antenna is formed over the first surface of the internal substratum; [[and]]

a wiring formed on the second surface of the internal substratum; and  
a cover for covering around the internal substratum,  
wherein the wiring is electrically connected to the thin film transistor and a part of  
the antenna through a contact hole formed in the internal substratum.

28. (Original) The ID tag according to claim 27, wherein the antenna and the thin film integrated circuit device are connected through a cross wiring.

29. (Original) The ID tag according to claim 27, wherein the cover comprises resin and is formed by a laminating method.

30. (Currently Amended) The ID tag according to claim 27, wherein a protective layer comprising a single layer of stacked layers containing silicon oxide, silicon nitride of silicon oxynitride is formed on at least one of ~~[[the]]~~ an upper surface and ~~[[the]]~~ a lower surface of the thin film integrated circuit device.

31. (Currently Amended) An object comprising:  
a thin film integrated circuit device including a thin film transistor provided in contact with a substratum on which an antenna is formed; ~~[[and]]~~  
an insulating layer over the antenna;  
a wiring formed over the insulating layer; and  
a cover for covering at least a side in which the antenna and the thin film integrated circuit device are formed,  
wherein the wiring is connected to the antenna through a contact hole formed in  
the insulating layer.

32. (Currently Amended) The object according to claim 31, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride

or silicon oxynitride is formed on at least one of ~~[[the]]~~ an upper surface and ~~[[the]]~~ a lower surface of the thin film integrated circuit device.

33. (Currently Amended) An object comprising:

an internal substratum having a first surface and a second surface opposing to the first surface;

an antenna formed over the first surface of the internal substratum;

a thin film integrated circuit device including a thin film transistor ~~provided in contact with an internal substratum on which an antenna is formed~~ over the first surface of the internal substratum; ~~[[and]]~~

a wiring formed on the second surface of the internal substratum; and

a cover for covering around the internal substratum,

wherein the wiring is electrically connected to the thin film transistor and a part of the antenna through a contact hole formed in the internal substratum.

34. (Currently Amended) The object according to claim 33, wherein a protective layer comprising a single layer or stacked layers containing silicon oxide, silicon nitride or silicon oxynitride is formed on at least one of ~~[[the]]~~ an upper surface and ~~[[the]]~~ a lower surface of the thin film integrated circuit device.

35. (Currently Amended) An ID label comprising:

a label substratum having a first surface and a second surface opposing to the first surface;

an antenna formed over the first surface of the label substratum;

a thin film integrated circuit device including a thin film transistor, over the first surface of the label substratum;

a wiring formed on the second surface of the label substratum;

a separating sheet provided over the first surface of the label substratum with an adhesive layer, antenna, and the thin film integrated circuit device interposed therebetween,

wherein the wiring is electrically ~~connect~~ connected to the thin film transistor and a part of the antenna through a contact hole formed in the label substratum.

36. (Currently Amended) An ID label comprising:

a label substratum;

an antenna formed over the label substratum;

an insulating layer over the antenna;

a wiring formed on the insulating layer;

a thin film integrated circuit device including a thin film transistor, over the label substratum;

a separating sheet provided over the label substratum with an adhesive layer, the antenna, and the insulating layer, and the thin film integrated circuit device interposed therebetween,

wherein the wiring is connected to the antenna through a contact hole formed in the insulating layer.